

Methoden moderner Röntgenphysik: Streuung und Abbildung

Lecture 4	Vorlesung zum Haupt- oder Masterstudiengang Physik, SoSe 2019 G. Grübel, L. Müller, O. Seeck, L. Frenzel, F. Lehmkuhler, M. Martins, W. Wurth
Location	Lecture hall AP, Physics, Jungiusstraße
Date	Tuesdays 12:30 - 14:00 (starting 2.4.) Thursdays 8:30 - 10:00 (until 11.7.)

Methoden moderner Röntgenphysik: Streuung und Abbildung

Part I:

Basics of X-ray Physics

by Gerhard Grübel (GG)

- [2.4.] Organisation and Introduction
- [4.4.] X-ray Scattering Primer
- [9.4.] Sources of X-rays, Synchrotron Radiation
- [11.4.] Refraction and Reflection
- [16.4.] Kinematical Scattering Theory (I)
- [18.4.] Kinematical Scattering Theory (II), Applications
- [23.4.] Small Angle Scattering and Soft Matter
- [25.4.] Anomalous Scattering
- [30.4.] Introduction: Coherence I
- [2.5.] Coherence II; Applications of Coherent X-ray Beams

Methoden moderner Röntgenphysik: Streuung und Abbildung

Part I:

Basics of X-ray Physics

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Introduction

Overview, Introduction to X-ray Scattering

X-ray Scattering Primer

Elements of X-ray Scattering

Sources of X-rays, Synchrotron Radiation

Laboratory Sources, Accelerator Bases Sources



Reflection and Refraction from Interfaces

Snell's Law, Fresnel Equations

Kinematical Diffraction (I)

Diffraction from an Atom, a Molecule, from Liquids, Glasses, ...

Kinematical Diffraction (II)

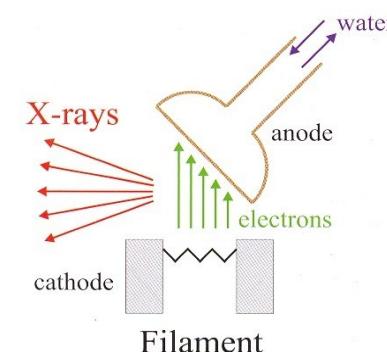
Diffraction from a Crystal, Reciprocal Lattice, Structure Factor, ...

Source of X-Rays

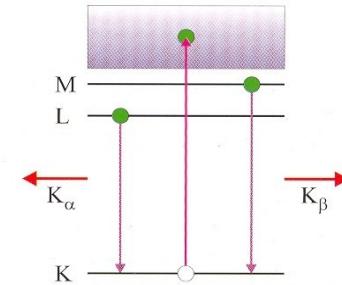
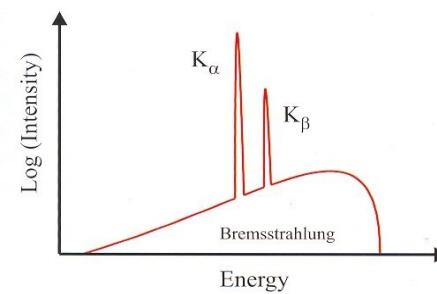
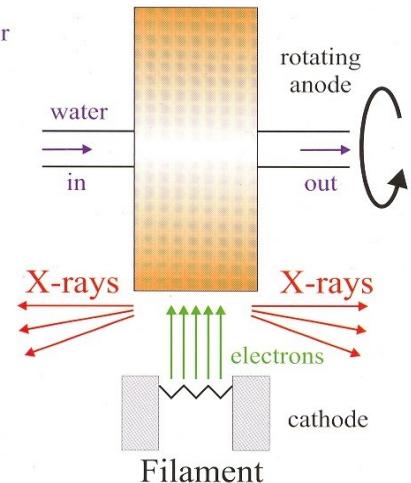
- 1895 Discovered by W.C. Röntgen
- 1912 First diffraction experiment (v. Laue)
- 1912 Coolidge tube (W.D. Coolidge, GE)
- 1946 Radiation from electrons in a synchrotron, GE,
Physical Review, 71,829 (1947)



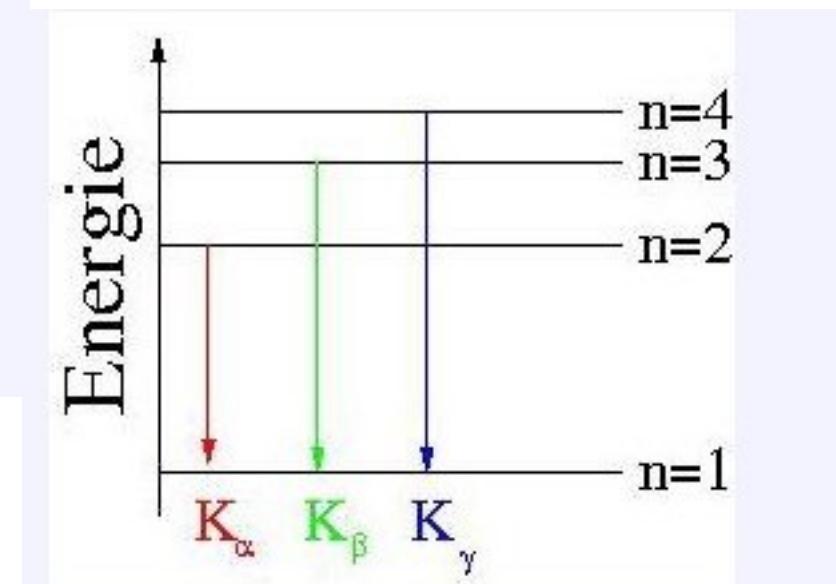
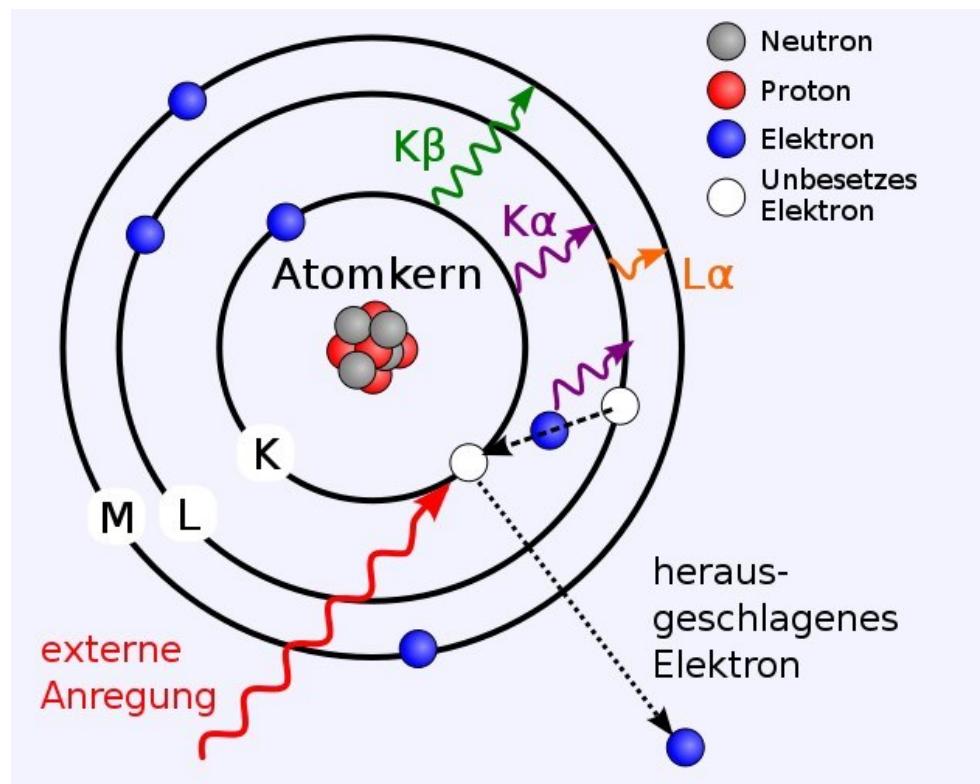
Coolidge Tube



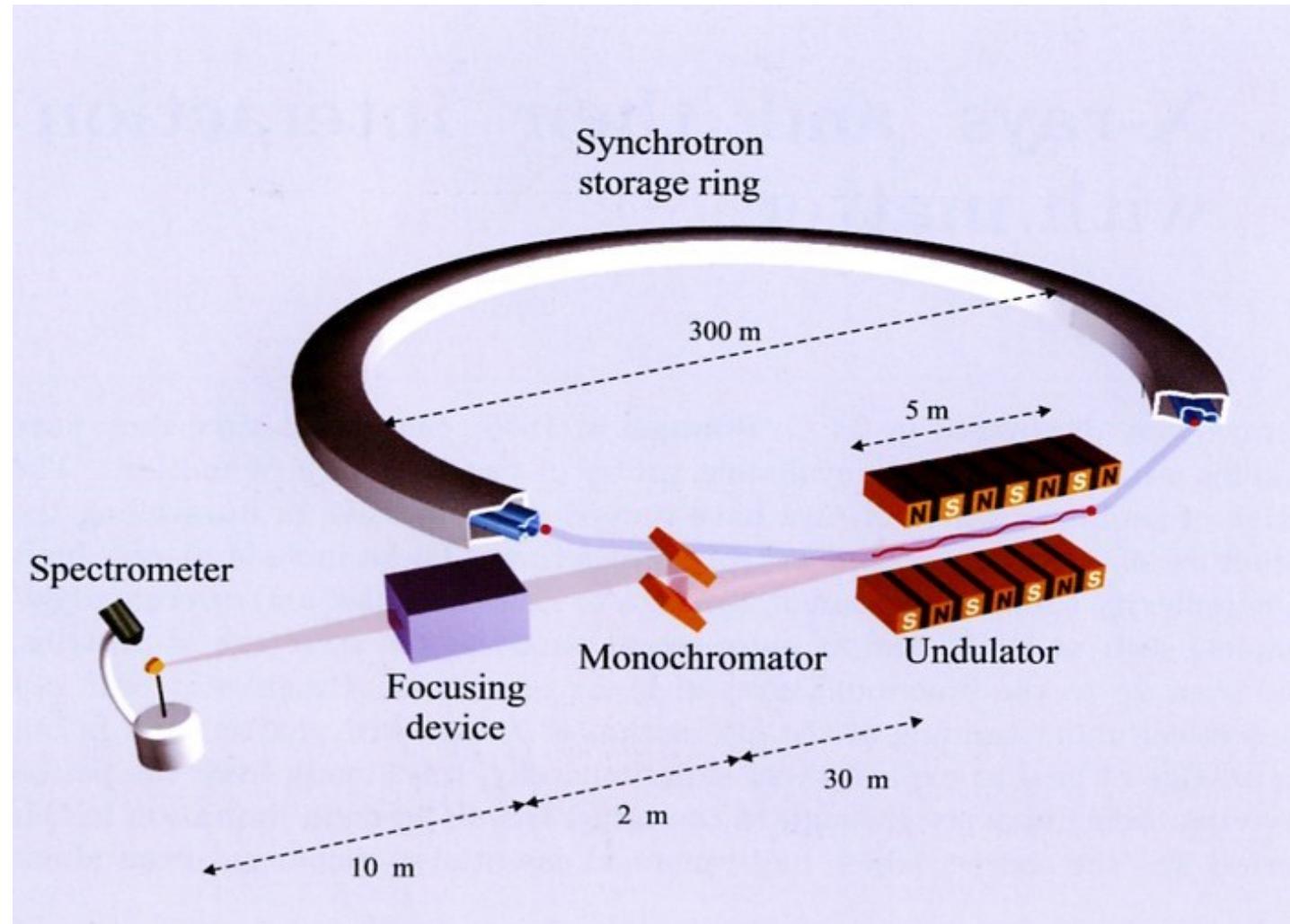
Rotating Anode



X-Ray Tube

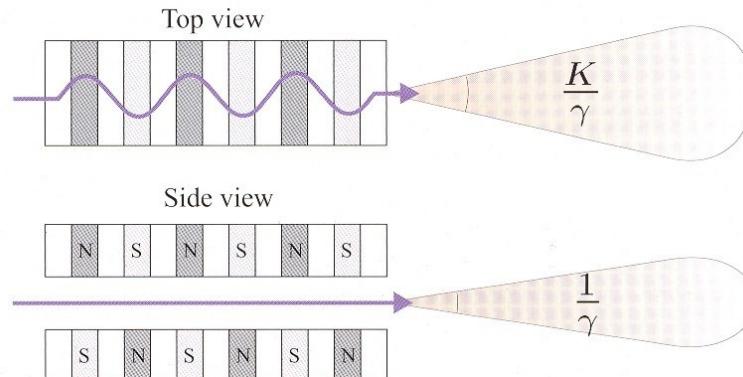


Synchrotron Radiation Storage Ring

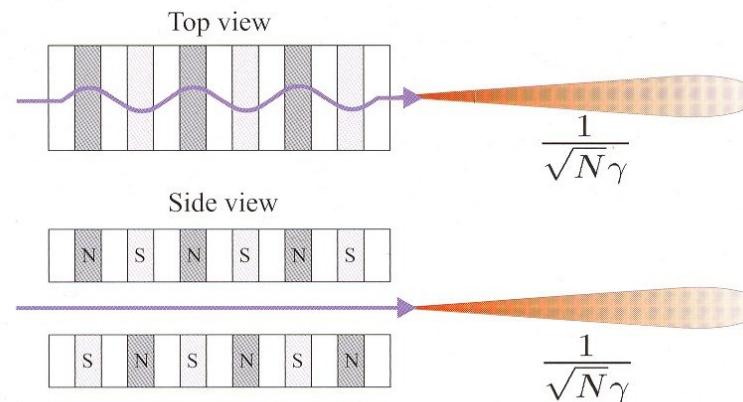


Insertion Devices (Wiggler and Undulators)

(a) Wiggler



(b) Undulator



Wiggler:

$$P[\text{kW}] = 0.633 E_e^2 [\text{GeV}] B^2 [\text{T}] L[\text{m}] I[\text{A}]$$

$$\text{Flux} \sim E^2 \times N$$

N: number poles

Undulator:

$$k = eB / mc \quad k_u = 0.934 \lambda_u [\text{cm}] \quad B_0 [\text{T}]$$

with λ_u undulator period

undulator fundamental:

$$\lambda_0 = \frac{\lambda_u}{2\gamma^2} \left(1 + \frac{k^2}{2} + \cancel{\gamma_0} \right)$$

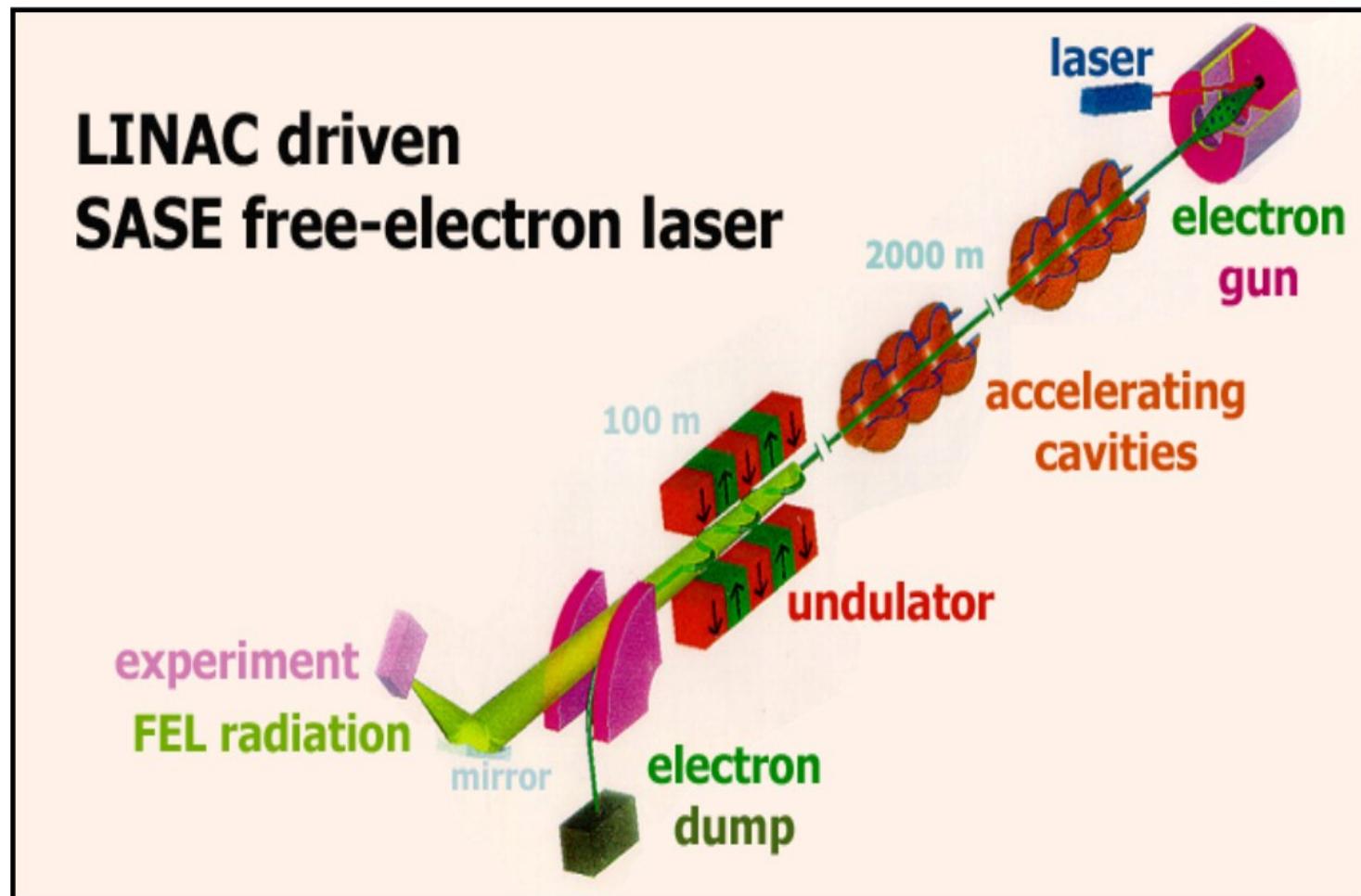
~~on axis~~

$$\text{Flux} \sim E^2 \times N^2$$

$$\text{bandwidth: } \frac{\Delta\lambda}{\lambda} \sim \frac{1}{nN}$$



Free Electron Lasers (FELs)



Methoden moderner Röntgenphysik II: Streuung und Abbildung

Introduction

Overview, Introduction to X-ray Scattering

X-ray Scattering Primer

Elements of X-ray Scattering

Sources of X-rays, Synchrotron Radiation

Laboratory Sources, Accelerator Bases Sources

Reflection and Refraction from Interfaces

Snell's Law, Fresnel Equations



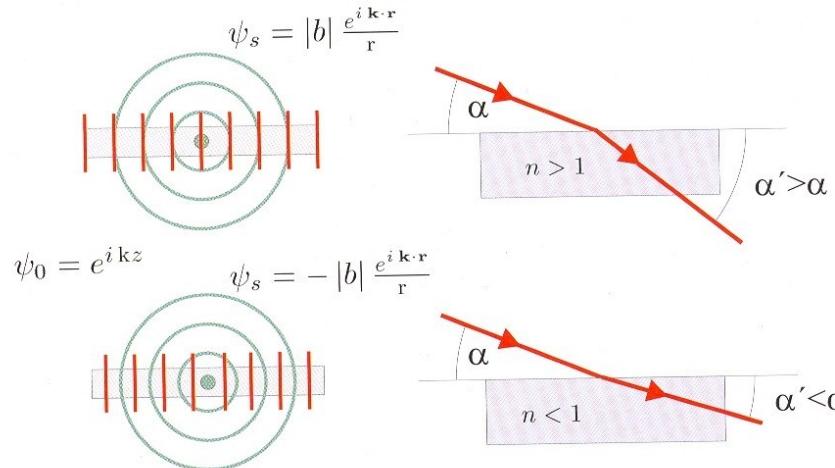
Kinematical Diffraction (I)

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Kinematical Diffraction (II)

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Reflection and Refraction from Interfaces



Note: spherical wave $e^{ik'r}$

$$k' = nk = \left(\frac{n}{c}\right) \omega = \frac{\omega}{v}$$

with $v = \frac{n}{c}$ phase velocity

($v > c$ for $n < 1$; but group velocity $\frac{d\omega}{dk} \leq c$)

Rays of light propagating in air change direction when entering glass, water or another transparent material.

Governed by Snell's law:

$$\frac{\cos \alpha}{\cos \alpha'} = n \text{ (refractive index)}$$

$$n = n(\omega) \quad 1.2 < n < 2 \text{ visible light}$$

$$n < 1 \text{ X-rays } (\alpha' < \alpha)$$

$$n = 1 - \delta \quad \delta \approx 10^{-5}$$

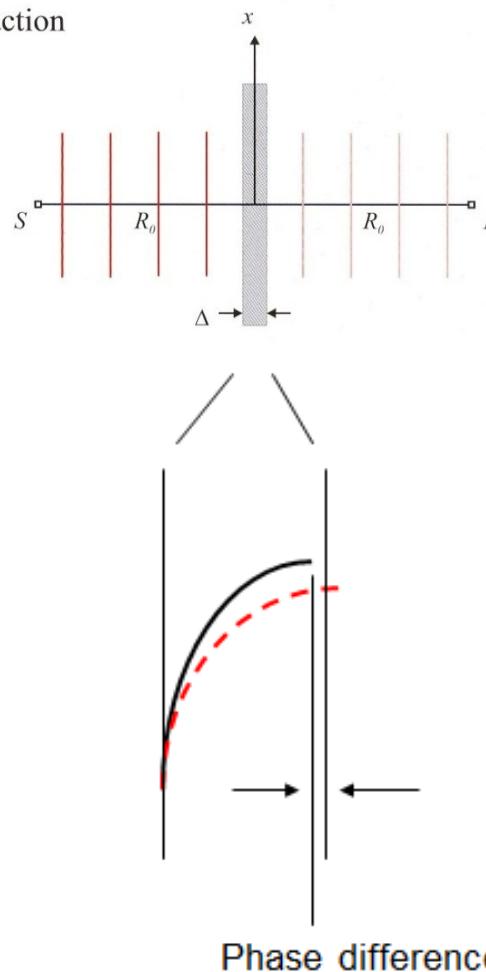
Total external reflection:

for $\alpha < \alpha_c$ (critical angle)



Refractive Index

Refraction



Refractive picture:

Consider plane wave impinging on a slab with thickness Δ and refractive index n . Evaluate amplitude at observation point P (compared to the situation without slab).

$$\text{no slab: } e^{ik\Delta}$$

$$\text{slab: } e^{ink\Delta}$$

$$\left. \begin{array}{l} \text{phase difference:} \\ e^{i(nk-k)\Delta} \end{array} \right]$$

Amplitude:

$$\frac{\psi_{\text{tot}}^P}{\psi_0^P} = \frac{e^{ink\Delta}}{e^{ik\Delta}}$$

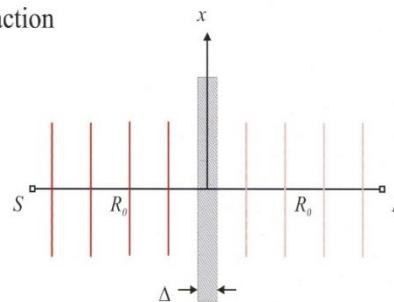
$$= e^{i(nk-k)\Delta}$$

$$e^{i\alpha} = \cos \alpha + i \sin \alpha \quad \xrightarrow{\alpha \text{ small}} \quad 1 + i\alpha$$

$$\boxed{\psi_{\text{tot}}^P \approx \psi_0^P [1 + i k(n - 1)\Delta]} \quad (\$)$$

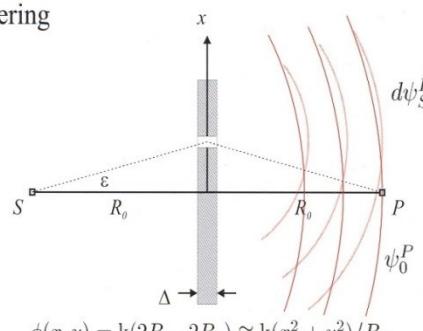
Refractive Index

Refraction



$$\psi_{tot}^P = \psi_0^P e^{i(nk-k)\Delta} \approx \psi_0^P [1 + i(n-1)k\Delta]$$

Scattering



$$\phi(x, y) = k(2R - 2R_0) \approx k(x^2 + y^2)/R_0$$

$$d\psi_s^P = \left(\frac{e^{ikR_0}}{R_0}\right) \text{ incident wave}$$

$$(\rho \Delta dx dy) \text{ number of scatterers}$$

$$\left(-b \frac{e^{ikR_0}}{R_0}\right) \text{ spherical wave from one scatterer}$$

$$e^{i\phi(x, y)} \text{ apart from this phase factor}$$

$$\psi_{tot}^P = \psi_0^P + \int d\psi_s^P = \psi_0^P \left[1 - i \frac{2\pi \rho b \Delta}{k} \right]$$

Scattering picture:

$$R = \sqrt{R_0^2 + x^2} = \sqrt{R_0^2 \left(1 + \frac{x^2}{R_0^2}\right)} \approx R_0 \sqrt{1 + \frac{x^2}{R_0^2} + \frac{x^4}{4R_0^2}}$$

$$= R_0 \sqrt{\left(1 + \frac{x^2}{2R_0^2}\right)^2} = R_0 \left(1 + \frac{x^2}{2R_0^2}\right)$$

phase difference ($2kR$) between direct rays and rays following path R ;

$$\frac{2kx^2}{2R_0} = \frac{kx^2}{R_0}$$

Include y direction: $e^{i\Phi(x, y)} = e^{\frac{i(x^2+y^2)k}{R_0}}$

Amplitude at P:

$$d\psi_s^P \approx$$

$$e^{\frac{ikR_0}{R_0}}$$

$$(\rho \Delta dx dy)$$

$$\left(b e^{\frac{ikR_0}{R_0}}\right)$$

$$e^{i\Phi(x, y)}$$



incident wave number of scatters in volume element $\rho dx dy$

scattered wave from 1 scatterer

phase factor



Refractive Index

$$\Psi_s^P = \int d\Psi_s^P = -\rho b \Delta \left(\frac{\exp(i2kR_0)}{R_0^2} \right) \int \exp(i\Phi(x,y)) dx dy \quad [1]$$

$i \frac{\pi R_0}{k}$ [Ref. 1]

Amplitude at P without slab:

$$\Psi_0^P = \left(\frac{\exp(i2kR_0)}{2R_0} \right) \quad [2]$$

$$\begin{aligned} \Psi_{\text{tot}}^P &= [1] + [2] = \Psi_0^P \left[1 - \left(\frac{i2\pi\rho b \Delta}{k} \right) \right] \\ &\equiv (\$) \equiv \Psi_0^P [1 + i(n - 1)k\Delta] \end{aligned}$$

→ $n = 1 - \frac{2\pi\rho b}{k^2} = 1 - \delta$

$$k = \frac{2\pi}{\lambda} = 4\text{\AA} - 1, \quad b = r_0 = 2.82 \times 10^{-5}\text{\AA}, \quad \rho = \frac{1e^-}{\text{\AA}^3}: \delta \approx 10^{-5} \quad [\text{Ref. 1: Als-Nielsen and McMorrow, p. 66}]$$

If a homogenous electron density ρ is replaced by a plate composed of atoms:

$$\rho = \rho_a f^0(0)$$

number density x atomic scattering factor

$$\delta = \frac{2\pi\rho_a f^0(0)r_0}{k}$$

Total external reflection ($\alpha' = 0$) for $\alpha = \alpha_c$:

$$\cos \alpha = n \cos \alpha'$$

$$\cos \alpha_c = 1 - \frac{\alpha_c^2}{2}$$

$$\alpha_c = \sqrt{2\delta} = \sqrt{\frac{4\pi\rho r_0}{k^2}}$$



Critical Angle for Si

$$\alpha_c = \sqrt{2\delta} = \sqrt{\frac{4\pi\rho r_0}{k^2}}$$

Silicon: $\rho = \frac{0.699e^-}{\text{\AA}^3}$, $\lambda = 1\text{\AA}$

$$\begin{aligned}\alpha_c &= \sqrt{(4\pi \times 0.699 \times 2.82e^{-5}) \times \frac{1}{(2\pi)^2}} \\ &= 0.0025 \text{ rad}\end{aligned}$$

$$Q_c = \left(\frac{4\pi}{\lambda}\right) \sin \alpha_c = 0.032 \text{\AA}^{-1}$$

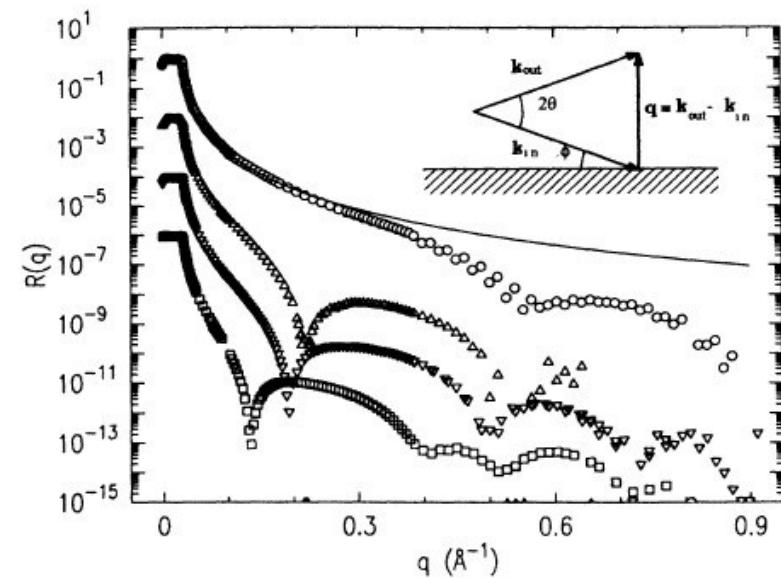
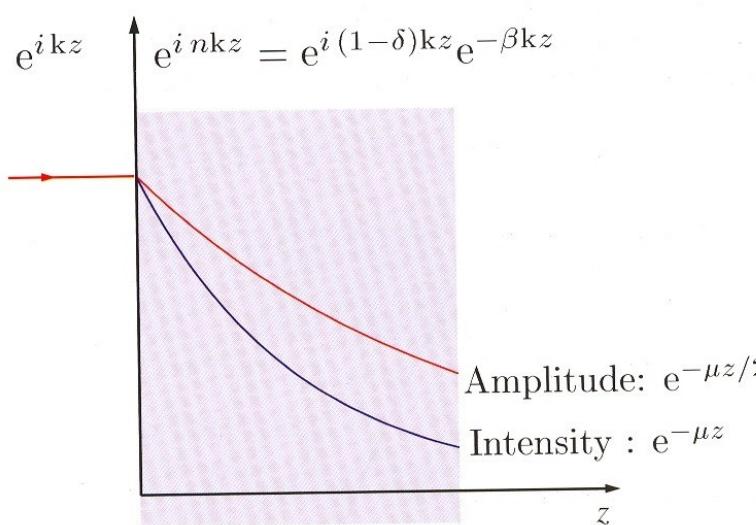


FIG. 1. Normalized reflectivity data from several samples. Successive data sets are displaced by 100 times and error bars omitted for clarity. (—) Theoretical reflectivity from an ideal step interface with bulk silicon density. (○) Uncoated silicon sample in helium; the “pairing” of points occurs for two scans taken 60 min apart and is probably due to the build up of contaminants on the surface. (△) 10-carbon chain alkylsiloxane. (▽) 12-carbon chain alkylsiloxane. (□) 18-carbon chain alkylsiloxane. The inset shows a schematic diagram of the scattering vectors for the specular reflectivity condition, where $2(\phi)=2\theta$.

Refraction Including Absorption



$$n = 1 - \delta + i \beta$$

Wave propagating in a medium:

$$e^{i n k z} = e^{i(1 - \delta)kz} e^{-\beta k z}$$

Attenuation of amplitude: $e^{-\frac{\mu z}{2}}$

(when intensity drops according to $e^{-\mu z}$)

$$\beta = \frac{\mu}{2k}$$

$$n = 1 \quad n = 1 - \delta + i \beta$$

Snell's Law and the Fresnel Equations

Snell's Law and the Fresnel Equations

$$k = |\mathbf{k}_I| = |\mathbf{k}_R|$$

$$\parallel: a_I k \cos \alpha + a_R k \cos \alpha = a_T (nk) \cos \alpha' \quad (B')$$

$$\perp: -(a_I - a_R)k \sin \alpha = -a_T (nk) \sin \alpha' \quad (B'')$$

$$\boxed{\cos \alpha = n \cos \alpha'} \quad (B'+A)$$

$$\underline{\alpha, \alpha' \text{ small}}: (\cos z = 1 - \frac{z^2}{2})$$

$$\alpha^2 = \alpha'^2 + 2\delta - 2i\beta$$

$$= \alpha'^2 + \alpha_c^2 - 2i\beta \quad (C)$$

Assume that the wave and its derivative is continuous at the interface:

$$a_I + a_R = a_T \quad (A)$$

$$a_I \mathbf{k}_I + a_R \mathbf{k}_R = a_T \mathbf{k}_T \quad (B)$$

$$\frac{a_I - a_R}{a_I + a_R} = n \frac{\sin \alpha'}{\sin \alpha} \approx \frac{\alpha'}{\alpha} \quad (B''+A)$$

Fresnel equations:

$$r = \frac{a_R}{a_I} = \frac{\alpha - \alpha'}{\alpha + \alpha'} ; \quad t = \frac{a_T}{a_I} = \frac{2\alpha}{\alpha + \alpha'}$$

r: reflectivity

t: transmittivity

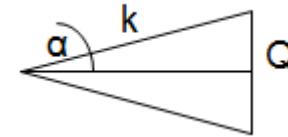


Snell's Law and the Fresnel Equations (2)

Note: α' is a complex number

$$\alpha' = \operatorname{Re}(\alpha') + i \operatorname{Im}(\alpha')$$

Use wavevector notation:



$$\sin \alpha = \frac{\left(\frac{Q}{2}\right)}{k}$$

Consider z-component of transmitted wave:

$$= a_T e^{ik \sin \alpha' z} \approx a_T e^{ik \alpha' z}$$

$$= a_T e^{ik \operatorname{Re}(\alpha') z} e^{-k \operatorname{Im}(\alpha') z}$$

↑
exponential damping

$$\text{intensity fall-off: } e^{-2k \operatorname{Im}(\alpha') z}$$

$$Q \equiv 2k \sin \alpha \approx 2k \alpha$$

$$Q_c \equiv 2k \sin \alpha_c \approx 2k \alpha_c$$

use dimensionless units:

$$q \equiv \frac{Q}{Q_c} \approx \left(\frac{2k}{Q_c}\right) \alpha ; \quad q' \equiv \frac{Q'}{Q_c} \approx \left(\frac{2k}{Q_c}\right) \alpha'$$

$$q^2 = q'^2 + 1 - 2i b_\mu$$

(D)

$$\Lambda = \frac{1}{2k \operatorname{Im}(\alpha')}$$

$$b_\mu = \left(\frac{2k}{Q_c}\right)^2 \beta = \left(\frac{4k^2}{Q_c^2}\right) \frac{\mu}{2k} = \frac{2k}{Q_c^2} \mu$$

$$Q_c = 2k\alpha_c = 2k\sqrt{2\delta}$$



Snell's Law and the Fresnel Equations (3)

Use table to extract μ , ρ , f' yielding Q_c

and calculate b_μ ($b_\mu \ll 1$):

$$b_\mu = \frac{2k\mu}{Q_c^2}$$

Use (D): $q^2 = q'^2 + 1 - 2 i b_\mu$

	Z	Molar density (g/mole)	Mass density (g/cm ³)	ρ (e/Å ³)	Q_c (1/Å)	$\mu \times 10^6$ (1/Å)	b_μ
C	6	12.01	2.26	0.680	0.031	0.104	0.0009
Si	14	28.09	2.33	0.699	0.032	1.399	0.0115
Ge	32	72.59	5.32	1.412	0.045	3.752	0.0153
Ag	47	107.87	10.50	2.755	0.063	22.128	0.0462
W	74	183.85	19.30	4.678	0.081	33.235	0.0409
Au	79	196.97	19.32	4.666	0.081	40.108	0.0495

Get:

$$r(q) = \frac{q - q'}{q + q'}$$

$$t(q) = \frac{2q}{q + q'}$$

$$\Lambda(q) = \frac{1}{Q_c \text{Im}(q')}$$

Snell's Law and the Fresnel Equations (4)

Fresnel equations:

$$\mathbf{q} \gg 1: \quad R(Q) \sim \frac{1}{Q^4},$$

$$\Lambda \approx \mu^{-1},$$

$$T \approx 1,$$

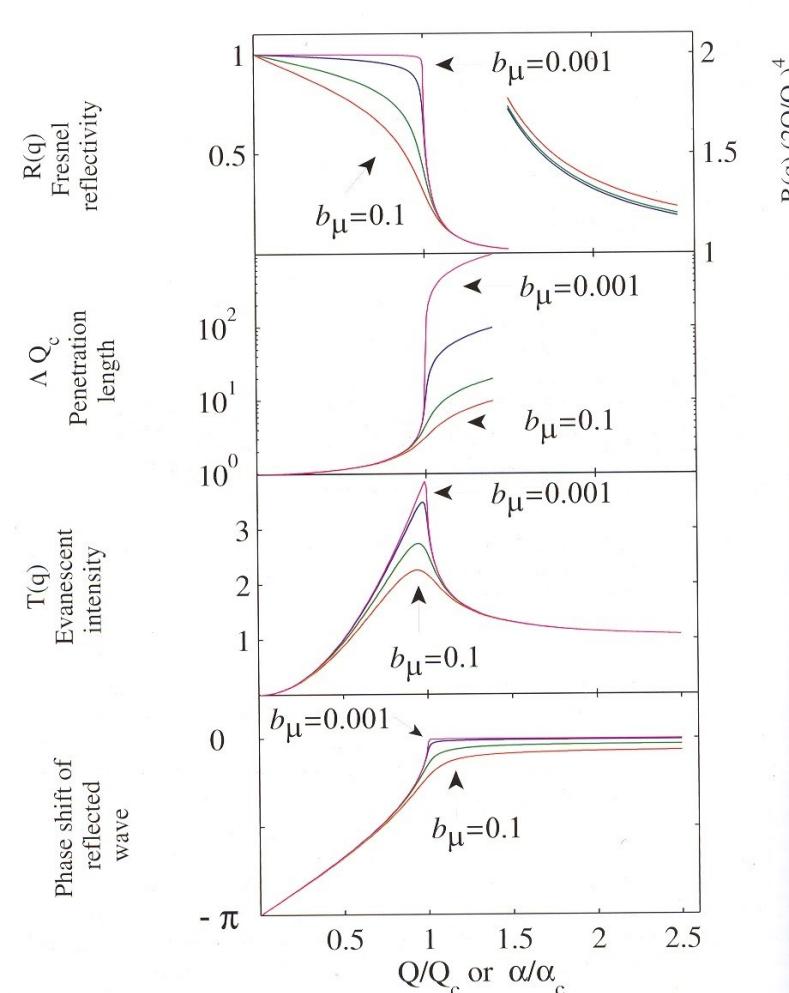
no phase shift

$$\mathbf{q} \ll 1: \quad R \approx 1, \\ \Lambda \approx \frac{1}{Q_c} \text{ small,}$$

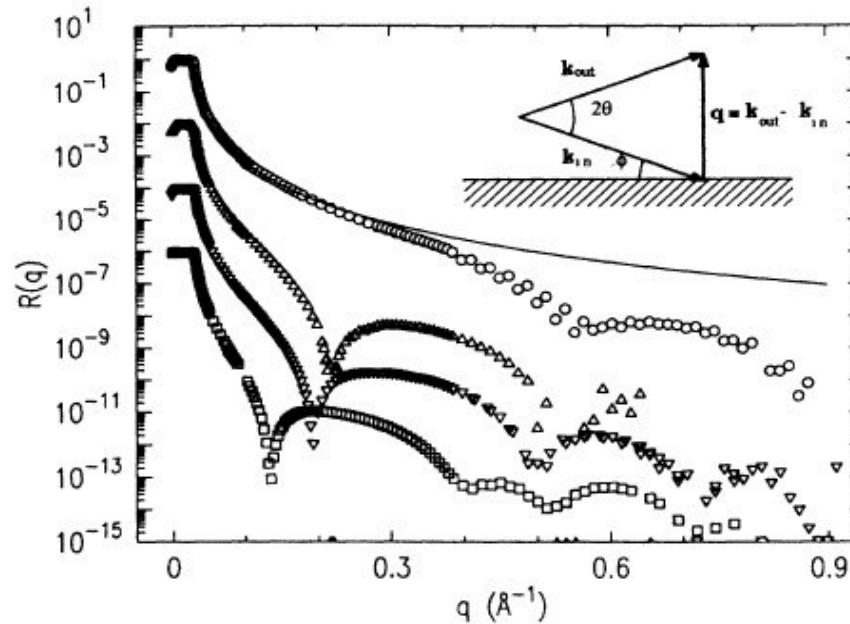
T very small,

$-\pi$ phase shift

$$\mathbf{q} = 1: \quad T(q=1) \approx 4a_I$$



Examples



PHYSICAL REVIEW B

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X-ray specular reflection studies of silicon coated by organic monolayers (alkylsiloxanes)

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